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Data Sheet
LED Display Chip   EODC-660-19-18   Rev. 01, 2014

Radiation	Type	Electrodes
Red	GaAsP/GaAs, diffusion type	p (anode) up

Application:

This miniature device is an excellent choice for applications where small size and reduced space are important factors such as complex displays in optical devices for laboratory, measurement, control- and medical equipment

Typ dimensions:

typ thickness: 290 µm
cathode: Au-alloy metalization
anode: Al metalization

all dimensions in µm

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Symbol	Cond.*	Min	Typ	Max	Unit
Forward voltage	V_F	I_F=10 mA		1.65	1.7	V
Reverse voltage	V_R	I_R=10 µA	5			V
Luminous intensity / segment**	I_V	I_F=10 mA	180	250		µcd
I_v ratio segment to segment**		I_F=10 mA			1.75	
I_v ratio to adjacent chip		I_F=10 mA			2	
Peak wavelength	λ_p	I_F=10 mA	650	660	670	nm
FWHM	$\Delta\lambda_{0.5}$	I_F=10 mA		17		nm

*Current for one segment   **Measured on bare chip on TO18 header

Miscellaneous Parameters

T_{amb}= 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Temperature coefficient of λ_C	T_a = -40…+120°C	$TC(\lambda_C)$	0.15	nm/K
Operating temperature range		T_{amb}	-40 to +120	°C
Storage temperature range		T_{stg}	-40 to +125	°C

Packing

Art. No. 115 011   Dice on adhesive film with wire-bond on top

RoHS COMPLIANT   Pb Pb-Free